

Schematic components that have been frozen by the user will appear with blue reference designators.

Power Supply Input

Var	Value	Units	Description
VACMIN	85	V	Minimum Input AC Voltage
VACMAX	265	V	Maximum Input AC Voltage
FL	50	Hz	Line Frequency
TC	2.69	ms	Input Rectifier Conduction Time
Z	0.56		Loss Allocation Factor
η	80.0	%	Efficiency Estimate (Target)
VMIN	82.2	V	Minimum DC Input Voltage
VMAX	374.8	V	Maximum DC Input Voltage

Input Section

Var	Value	Units	Description
Fuse	1.00	A	Input Fuse Rated Current
I _{AVG}	0.64	A	Average Diode Bridge Current (DC Input Current)
Thermistor	8.00	Ω	Input Thermistor (Manual Overwrite)

Device Variables

Var	Value	Units	Description
Device	TOP256YN		PI Device Name
BVDSS	700	V	Drn-Src Bkdn Voltage
Current Limit Mode	Default		Device Current Limit Mode
OVP_FLAG	NO		Output Overvoltage Protection Enabled
PO	42.07	W	Total Output Power
V _{DRAIN} Estimated	588.49	V	Estimated Drain Voltage
V _{DS}	9.96	V	On state Drain to Source Voltage
FS	132000	Hz	Switching Frequency (at V _{MIN} and Full Load)
KP	0.500		Continuous/Discontinuous Operating Ratio (at V _{MIN} and Full Load)
D _{MAX}	0.560		Maximum Duty Cycle (at V _{MIN} and Full Load)
KI	0.94		Current Limit Reduction Factor (Manual Overwrite)
I _{LIMITTEXT}	2.23	A	Programmed Current Limit
I _{LIMITMIN}	2.372	A	Minimum Current Limit
I _{LIMITMAX}	2.729	A	Maximum Current Limit
PLIM_FLAG	NO		Enable Overload Power Limiting (Manual Overwrite)
I _P	1.523	A	Peak Primary Current (at V _{MIN} and Full Load)
I _{RMS}	0.870	A	Primary RMS Current (at V _{MIN} and Full Load)
R _{TH_DEVICE}	17.27	$^{\circ}\text{C}/\text{W}$	PI Device Heatsink Maximum Thermal Resistance
DEV_HSINK_TYPE	Custom Aluminum		PI Device Heatsink Type
DEV_HSINK_AREA	4376	mm ²	PI Device Heatsink Area

Clamp Circuit

Var	Value	Units	Description
Clamp Type	RCD Clamp		Clamp Circuit Type (Manual Overwrite)
V _{CLAMP}	121.72	V	Average Clamping Voltage
Estimated Clamp Loss	1.384	W	Clamp total power loss
V _{C_MARGIN}	133.23	V	Clamp Voltage Safety Margin

Primary Bias Variables

Var	Value	Units	Description
VB	15.0	V	Bias Voltage
IB	0.006	A	Bias Current
PIVB	82	V	Bias Rectifier Maximum Peak Inverse Voltage
NB	10		Primary Bias Winding Number of Turns

Transformer Construction Parameters

Var	Value	Units	Description
Core Type	ETD29/16/10		Core Type (Manual Overwrite)
Core Material	3C95		Core Material
Bobbin Reference	Generic, 7 pri. + 7 sec.		Bobbin Reference
Bobbin Orientation	Horizontal		Bobbin type
Primary Pins	5		Number of Primary pins used
Secondary Pins	6		Number of Secondary pins used
USE_SHIELDS	NO		Use shield Windings
LP_nom	447	μ H	Nominal Primary Inductance
LP_Tol	10.0	%	Primary Inductance Tolerance
NP	55.8		Calculated Primary Winding Total Number of Turns
NSM	8		Secondary Main Number of Turns
CMA	464.12	Cmils/A	Primary Winding Current Capacity
VOR	92.00	V	Reflected Output Voltage (Manual Overwrite)
BW	19.40	mm	Bobbin Winding Width
ML	0.00	mm	Safety Margin on Left Width
MR	0.00	mm	Safety Margin on Right Width
FF	72.22	%	Actual Transformer Fit Factor. 100% signifies fully utilized winding window
AE	76.00	mm ²	Core Cross Sectional Area
ALG	129	nH/T ²	Gapped Core Specific Inductance
BM	1445	Gauss	Maximum Flux Density
BP	2434	Gauss	Peak Flux Density
BAC	361	Gauss	AC Flux Density for Core Loss
LG	0.693	mm	Estimated Gap Length
L_LKG	11.17	μ H	Estimated primary leakage inductance
LSEC	10	nH	Secondary Trace Inductance

Primary Winding Section 1

Var	Value	Units	Description
NP1	28		Number of Primary Winding Turns in the First Section of Primary
Wire Size	24	AWG	Primary Winding - Wire Size (Manual Overwrite)
Winding Type	Single (x1)		Primary Winding - Number of Parallel Wire Strands (Manual Overwrite)
L	0.82		Primary Winding - Number of Layers
DC Copper Loss	0.09	W	Primary Section 1 DC Losses

Primary Winding Section 2

Var	Value	Units	Description
NP2	28		Rounded (Integer) Number of Primary winding turns in the second section of primary
Wire Size	24	AWG	Primary Winding - Wire Size

Winding Type	Single (x1)		Primary Winding - Number of Parallel Wire Strands (Manual Overwrite)
L2	0.82		Primary Number of Layers in 2nd split winding

Output 1

Var	Value	Units	Description
VO	12.00	V	Typical Output Voltage
IO	2.50	A	Output Current
VOUT_ACTUAL	12.00	V	Actual Output Voltage
NS	8		Secondary Number of Turns
Wire Size	25	AWG	Wire size of secondary winding
Winding Type	Trifilar (x3)		Output winding number of parallel strands
L_S_OUT	0.80		Secondary Output Winding Layers
DC Copper Loss	0.28	W	Secondary DC Losses
VD	1.20	V	Output Winding Diode Forward Voltage Drop (Manual Overwrite)
VD	1.20	V	Output Winding Diode Forward Voltage Drop (Manual Overwrite)
PIVS	65.54	V	Output Rectifier Maximum Peak Inverse Voltage
ISP	7.568	A	Peak Secondary Current
ISRMS	3.834	A	Secondary RMS Current
ISRMS_WINDING	3.834	A	Secondary Winding RMS Current
CMAS	251	Cmils/A	Secondary Winding Current Capacity
RTH_RECTIFIER	18.96	°C/W	Output Rectifier Heatsink Maximum Thermal Resistance
OR_HSINK_TYPE	1 Oz (35 µ) 2-Sided Copper PCB		Output Rectifier Heatsink Type
OR_HSINK_AREA	16112	mm ²	Output Rectifier Heatsink Area
CO	1800 x 1	µF	Output Capacitor - Capacitance
IRIPPLE	2.907	A	Output Capacitor - RMS Ripple Current
Expected Lifetime	44174	hr	Output Capacitor - Expected Lifetime

Output 2

Var	Value	Units	Description
VO	24.00	V	Typical Output Voltage
IO	0.50	A	Output Current
VOUT_ACTUAL	23.55	V	Actual Output Voltage
NS	15		Secondary Number of Turns
Wire Size	28	AWG	Wire size of secondary winding
Winding Type	Single (x1)		Output winding number of parallel strands (Manual Overwrite)
L_S_OUT	0.40		Secondary Output Winding Layers
DC Copper Loss	0.14	W	Secondary DC Losses
VD	1.20	V	Output Winding Diode Forward Voltage Drop (Manual Overwrite)
VD	1.20	V	Output Winding Diode Forward Voltage Drop (Manual Overwrite)
PIVS	123.93	V	Output Rectifier Maximum Peak Inverse Voltage
ISP	1.514	A	Peak Secondary Current
ISRMS	0.767	A	Secondary RMS Current
ISRMS_WINDING	0.767	A	Secondary Winding RMS Current

CMAS	207	Cmils/A	Secondary Winding Current Capacity
RTH_RECTIFIER	92.79	°C/W	Output Rectifier Heatsink Maximum Thermal Resistance
OR_HSINK_TYPE	1 Oz (35 μ) 2-Sided Copper PCB		Output Rectifier Heatsink Type
OR_HSINK_AREA	52	mm ²	Output Rectifier Heatsink Area
CO	150 x 1	μF	Output Capacitor - Capacitance
IRIPPLE	0.581	A	Output Capacitor - RMS Ripple Current
Expected Lifetime	31999	hr	Output Capacitor - Expected Lifetime

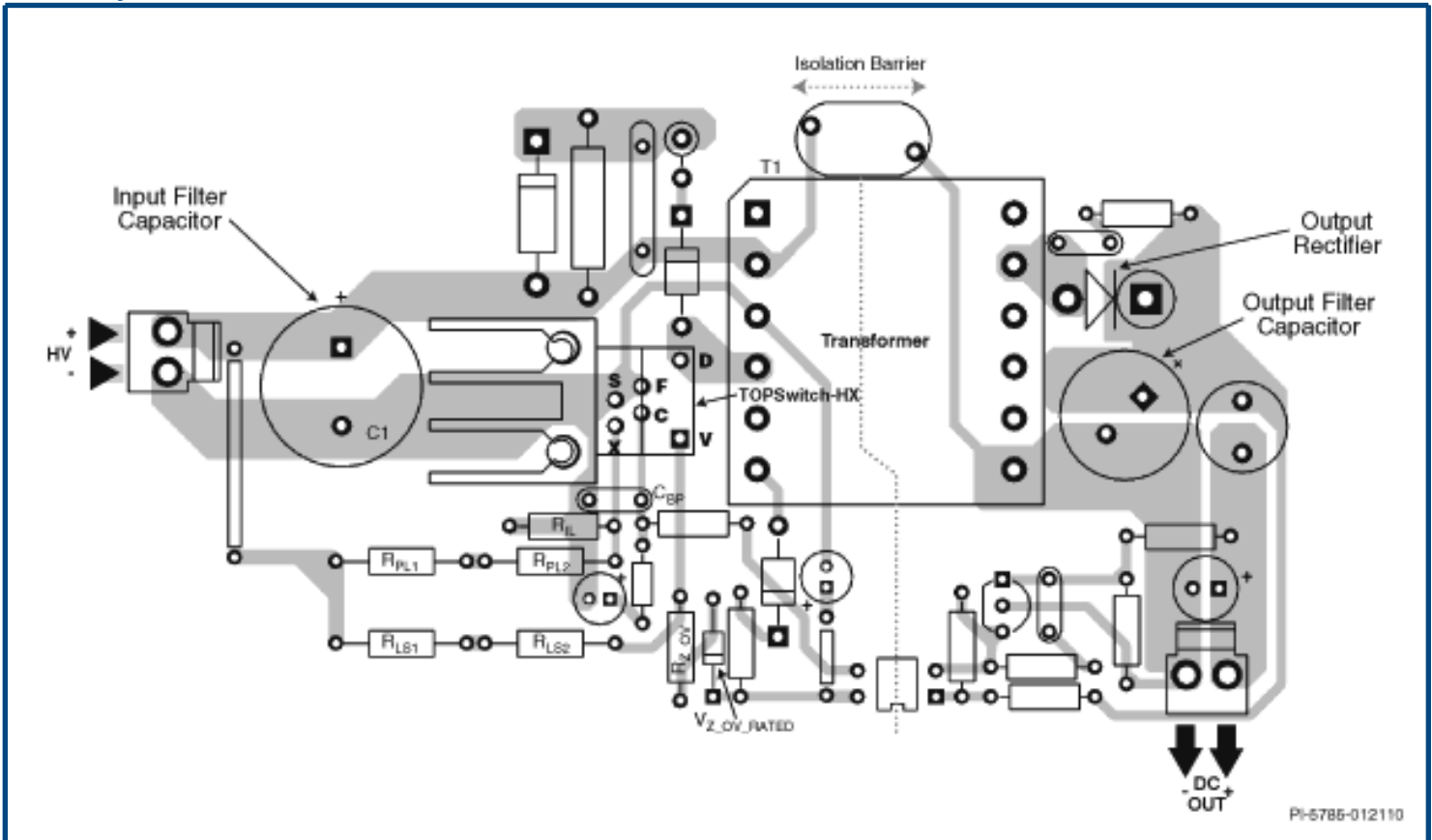
Feedback Circuit

Var	Value	Units	Description
DUAL_OUTPUT_FB_FLAG	NO		Get feedback from 2 outputs
SF_FLAG	NO		Soft Finish Circuits use flag
TYPE_3CTRL_FLAG	NO		Phase Boost Network flag

The regulation and tolerances do not account for thermal drifting and component tolerance of the output diode forward voltage drop and voltage drops across the LC post filter. The actual voltage values are estimated at full load only.

Please verify cross regulation performance on the bench.

Board Layout Recommendations



Click on the "Show me" icon to highlight relevant areas on the sample layout.

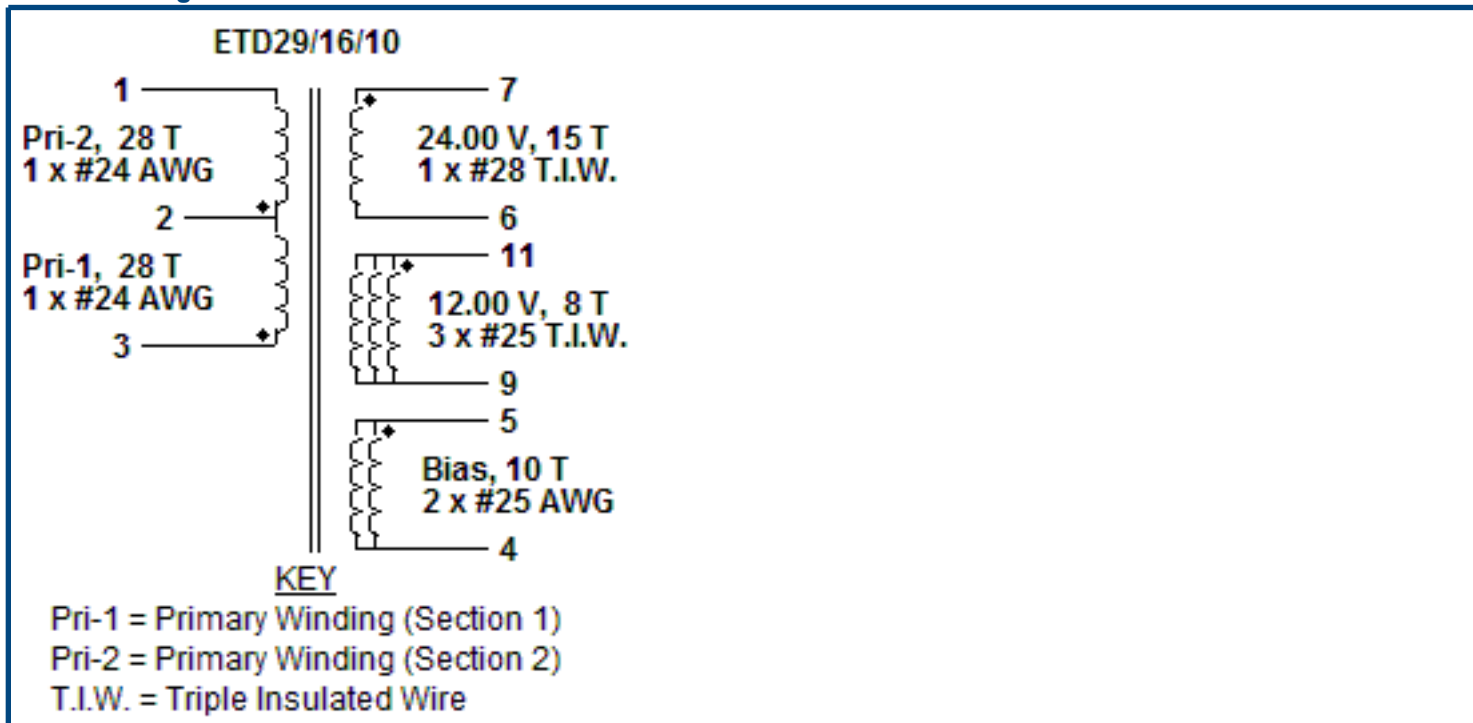
	Description	Show Me
1	Minimize loop area formed by drain, clamp and transformer	
2	Bias winding and bias capacitor are a power connection and therefore returned to Kelvin connection at SOURCE pin	
3	V and X pin node areas minimized, line sensing (R1 & R2) and power limiting (R3 & R4) close to device. Connections to V and X pin nodes should be away from noisy switching nodes (drain, clamp and bias)	
4	Place CONTROL pin decoupling capacitor directly across CONTROL and SOURCE pins	
5	Y capacitor connected between output RTN and B+	
6	Minimize loop area formed by secondary winding, the output rectifier and the output filter capacitor	
7	Kelvin connection at SOURCE pins: power and signal currents kept separate	
8	B+ connection of RLS or RPL resistor should be on input side of capacitor to prevent switching noise injection	

Bill Of Materials

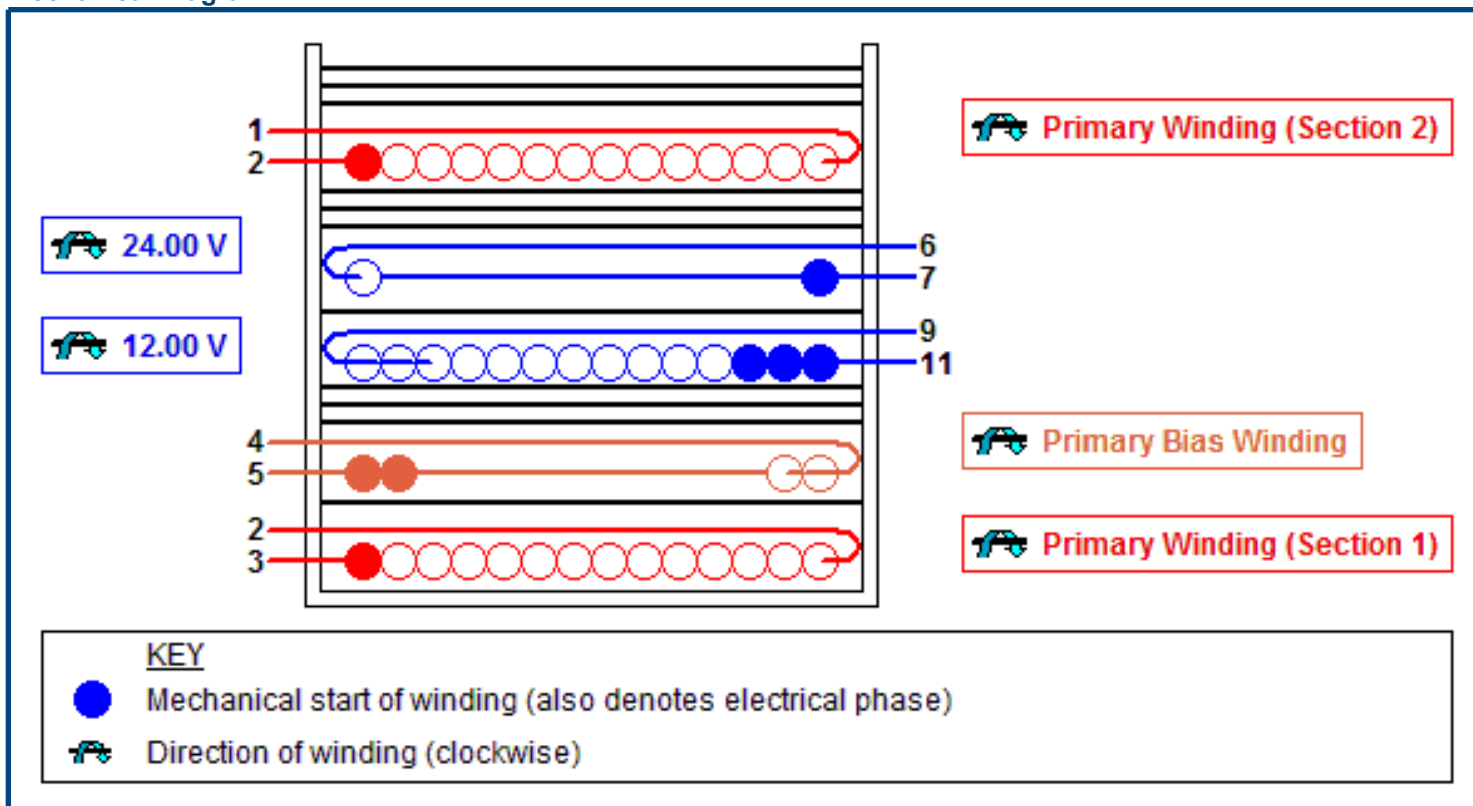
Ite m #	Quantity	Part Ref	Value	Description	Mfg	Mfg Part Number
1	1	BR1	DF1506S-T	600 V, 1.5 A, Standard Recovery Bridge, DFS	Diodes Inc.	DF1506S-T
2	1	C1	330 nF	330 nF, 275 VAC, Film, X Class	Panasonic	ECQ-UAAF334K
3	1	C2	100 μ F	100 μ F, 400 V, High Voltage Al Electrolytic, (30 mm x 16 mm)	United Chemi-Con	EPAG401ELL101ML30S
4	1	C3	3.3 nF	3.3 nF, 1 kV, High Voltage Ceramic	Kemet	C1206C332KDRACTU
5	2	C4, C14	0.1 μ F	0.1 μ F, 16 V, Ceramic, X7R	AVX Corp	0603YC104K4T4A
6	1	C5	47 μ F	47 μ F, 10.0 V, Electrolytic, Gen Purpose, 1000 m Ω , (5.2 mm x 6.3 mm)	United Chemi-Con	EMVY100ADA470MF55G
7	1	C6	0.68 nF	0.68 nF, 250 VAC, Ceramic, Y Class	Vishay Cera-Mite	440LT68-R
8	1	C7	27 pF	27 pF, 1 kV, High Voltage Ceramic	Murata	GRM31A5C3A270JW01D
9	1	C8	22 pF	22 pF, 630 V, High Voltage Ceramic	Murata	GRM31A5C2J220JW01D
10	1	C9	10 μ F	10 μ F, 50 V, Electrolytic, Gen Purpose, 1000 m Ω , (6.1 mm x 6.3 mm)	Rubycon	50TRV10M6.3X6.1
11	1	C10	1800 μ F	1800 μ F, 25 V, Electrolytic, Super Low ESR, 18 m Ω , (20 mm x 16 mm)	United Chemi-Con	EKZE250ELL182ML20S
12	1	C11	100 μ F	100 μ F, 25 V, Electrolytic, Low ESR, 260 m Ω , (8 mm x 6.2 mm)	Panasonic	EEEFK1E101AP
13	1	C12	150 μ F	150 μ F, 35 V, Electrolytic, Super Low ESR, 72 m Ω , (11.5 mm x 8 mm)	United Chemi-Con	EKZE350ELL151MHB5D
14	1	C13	100 μ F	100 μ F, 200 V, Electrolytic, Low ESR, 1900 m Ω , (21.5 mm x 18 mm)	Panasonic	EEVEB2D101M
15	1	D1	RS07K-GS08	800 V, 1.4 A, Fast Recovery, 300 ns, DO-219AB	Vishay	RS07K-GS08
16	1	D2	FDLL4448	100 V, 0.3 A, Fast Recovery, 4 ns, SOD-80	ON Semiconductor	FDLL4448
17	2	D3, D4	STTH3R02QRL	200 V, 3 A, Ultrafast Recovery, 20 ns, DO-15	STMicroelectronics	STTH3R02QRL
18	1	F1	1 A	250 VAC, 1 A, Radial TR5, Time Lag Fuse	Littelfuse / Wickmann(R)	37411000410
19	1	HS1		109.4 mm x 20 mm. Aluminum Alloy (3003 OR 5052), 1.6 mm thickness. Heatsink for use with Device U1.	Custom	
20	1	L1	6.8 mH	6.8 mH, 0.8 A	Panasonic	ELF15N008
21	2	L2, L3	3.3 μ H	3.3 μ H, 3.94 A	Eaton	DR74-3R3-R
22	2	R1, R2	1.1 M Ω	1.1 M Ω , 5 %, 0.25 W, Thick Film	Generic	
23	1	R3	33 k Ω	33 k Ω , 5 %, 2 W, Metal Oxide Film	Generic	
24	1	R4	5.1 Ω	5.1 Ω , 5 %, 0.25 W, Thick Film	Generic	
25	1	R5	6.65 k Ω	6.65 k Ω , 1 %, 0.125 W, Thick Film	Generic	
26	2	R6, R7	2 M Ω	2 M Ω , 1 %, 0.25 W, Thick Film	Generic	
27	1	R8	6.8 Ω	6.8 Ω , 5 %, 0.125 W, Thick Film	Generic	
28	1	R9	390 Ω	390 Ω , 5 %, 0.25 W, Thick Film	Generic	
29	1	R10	470 Ω	470 Ω , 5 %, 0.25 W, Thick Film	Generic	
30	1	R11	2000 Ω	2000 Ω , 1 %, 0.125 W, Thick Film	Generic	
31	1	R12	1 k Ω	1 k Ω , 5 %, 0.125 W, Thick Film	Generic	
32	1	R13	43.2 k Ω	43.2 k Ω , 1 %, 0.125 W, Thick Film	Generic	

33	1	R14	11.3 k Ω	11.3 k Ω , 1 %, 0.125 W, Thick Film	Generic	
34	1	RT1	8 Ω	NTC Thermistor 8 Ω , 3 A	Cornell Dubilier	SL12 8R003
35	1	T1	ETD29/16/10	3C95 Core Material See Transformer Construction's Materials List for complete information	Epcos	B66358-G-X127
36	1	U1	TOP256YN	TOPSwitch-HX, TOP256YN, TO-220	Power Integrations	TOP256YN
37	1	U2	LTV-826S	Optocoupler LTV-826S , 80 V, CTR 300 - 600 %, 4-SMD	Liteon	LTV-826S
38	1	U3	LM431ACM/NO PB	2.495 V, Shunt Regulator IC, 2 %, SOIC-8	Texas Instruments	LM431ACM/NOPB
39	1			16112 mm ² area on Copper PCB. 1 oz (35 μ m) thickness. Heatsink for use with Rectifier D3.	Custom	
40	1			52 mm ² area on Copper PCB. 1 oz (35 μ m) thickness. Heatsink for use with Rectifier D4.	Custom	

Electrical Diagram



Mechanical Diagram



Winding Instruction

Primary Winding (Section 1)

Start on pin(s) 3 and wind 28 turns (x 1 filar) of item [5]. in 1 layer(s) from left to right. Winding direction is clockwise. On the final layer, spread the winding evenly across entire bobbin. Finish this winding on pin(s) 2.

Add 1 layer of tape, item [3], for insulation.

Primary Bias Winding

Start on pin(s) 5 and wind 10 turns (x 2 filar) of item [6]. Winding direction is clockwise. Spread the winding evenly across entire bobbin. Finish this winding on pin(s) 4.

Add 3 layers of tape, item [3], for insulation.

Secondary Winding

Start on pin(s) 11 and wind 8 turns (x 3 filar) of item [7]. Spread the winding evenly across entire bobbin. Winding direction is clockwise. Finish this winding on pin(s) 9.

Add 1 layer of tape, item [3], for insulation.

Start on pin(s) 7 and wind 15 turns (x 1 filar) of item [8]. Spread the winding evenly across entire bobbin. Winding direction is clockwise. Finish this winding on pin(s) 6.

Add 3 layers of tape, item [3], for insulation.

Primary Winding (Section 2)

Start on pin(s) 2 and wind 28 turns (x 1 filar) of item [5]. in 1 layer(s) from left to right. Winding direction is clockwise. On the final layer, spread the winding evenly across entire bobbin. Finish this winding on pin(s) 1.

Add 3 layers of tape, item [3], for insulation.

Core Assembly

Assemble and secure core halves. Item [1].

Varnish

Dip varnish uniformly in item [4]. Do not vacuum impregnate.

Comments

1. Use of a grounded flux-band around the core may improve the EMI performance.

2. For non margin wound transformers use triple insulated wire for all secondary windings.

Materials

Item	Description
[1]	Core: E25/13/7 (EF25), 3C95, gapped for ALG of 119 nH/T ²
[2]	Bobbin: Generic, 7 pri. + 7sec.
[3]	Barrier Tape: Polyester film [1 mil (25 µm) base thickness], 15.30 mm wide
[4]	Varnish
[5]	Magnet Wire: 24 AWG, Solderable Double Coated
[6]	Triple Insulated Wire: 25 AWG
[7]	Triple Insulated Wire: 28 AWG
[8]	Magnet Wire: 25 AWG, Solderable Double Coated

Electrical Test Specifications

Parameter	Condition	Spec
Electrical Strength, VAC	60 Hz 1 second, from pins 1,2,3,4,5 to pins 6,7,9,11.	3000
Nominal Primary Inductance, µH	Measured at 1 V pk-pk, typical switching frequency, between pin 1 to pin 3, with all other Windings open.	447
Tolerance, ±%	Tolerance of Primary Inductance	10.0
Maximum Primary Leakage, µH	Measured between Pin 1 to Pin 3, with all other Windings shorted.	11.17

Although the design of the software considered safety guidelines, it is the user's responsibility to ensure that the user's power supply design meets all applicable safety requirements of user's product.

	Description	Fix	Ref. #
	<i>The Copper thickness is not recommended at this level of output power.</i>	<i>Change board thickness to 2</i>	179